

MOSFET – Power, Single, P-Channel, SC-70

-8.0 V, -1.4 A

NTS2101P

Features

- Leading Trench Technology for Low $R_{DS(on)}$ Extending Battery Life
- -1.8 V Rated for Low Voltage Gate Drive
- SC-70 Surface Mount for Small Footprint (2 x 2 mm)
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- Charging Circuit
- Single Cell Battery Applications such as Cell Phones, Digital Cameras, PDAs, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Units
Drain-to-Source Voltage	V_{DS}	-8.0	V
Gate-to-Source Voltage	V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	I_D	$T_A = 25^\circ\text{C}$	-1.4 A
		$T_A = 70^\circ\text{C}$	-1.1
		$t \leq 5\text{ s}$	-1.5 A
Power Dissipation (Note 1)	P_D	$T_A = 25^\circ\text{C}$	0.29 W
		$t \leq 5\text{ s}$	0.33 W
Pulsed Drain Current	I_{DM}	$t_p = 10\text{ }\mu\text{s}$	-3.0 A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode), Continuous	I_S	-0.46	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

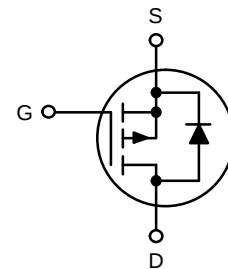
Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	430	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	375	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

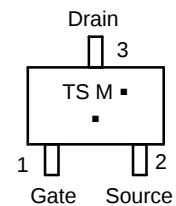
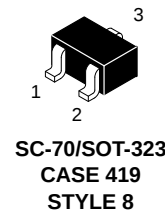
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
-8.0 V	65 m Ω @ -4.5 V	-1.4 A
	78 m Ω @ -2.5 V	
	117 m Ω @ -1.8 V	

P-Channel MOSFET



MARKING DIAGRAM & PIN ASSIGNMENT



TS = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

* Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTS2101PT1G	SOT-323 (Pb-Free)	3000/Tape & Reel

DISCONTINUED (Note 1)

NTS2101PT1	SOT-323	3000/Tape & Reel
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[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

NTS2101P

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-8.0	-20		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-10		mV/ $^{\circ}\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -6.4\text{ V}$	$T_J = 25\text{ }^{\circ}\text{C}$		-1.0	μA
			$T_J = 70\text{ }^{\circ}\text{C}$		-5.0	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-0.45	-0.7	-1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.6		mV/ $^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.0\text{ A}$		65	100	m Ω
		$V_{GS} = -2.5\text{ V}, I_D = -0.5\text{ A}$		78	140	
		$V_{GS} = -1.8\text{ V}, I_D = -0.3\text{ A}$		117	210	

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -8.0\text{ V}$		640		pF
Output Capacitance	C_{OSS}			120		
Reverse Transfer Capacitance	C_{RSS}			82		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5.0\text{ V}, V_{DD} = -5.0\text{ V}, I_D = -1.0\text{ A}$		6.4		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.7		
Gate-to-Source Charge	Q_{GS}			1.0		
Gate-to-Drain Charge	Q_{GD}			1.5		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -4.0\text{ V}, I_D = -1.0\text{ A}, R_G = 6.2\text{ }\Omega$		6.2		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			26		
Fall Time	t_f			18		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -0.3 A	T _J = 25 °C		-0.62	-1.2	V
			T _J = 125 °C		-0.51		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = -1.0 A			23.4		ns
Charge Time	T _a				7.7		
Discharge Time	T _b				15.7		
Reverse Recovery Charge	Q _{RR}					9.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL ELECTRICAL CHARACTERISTICS

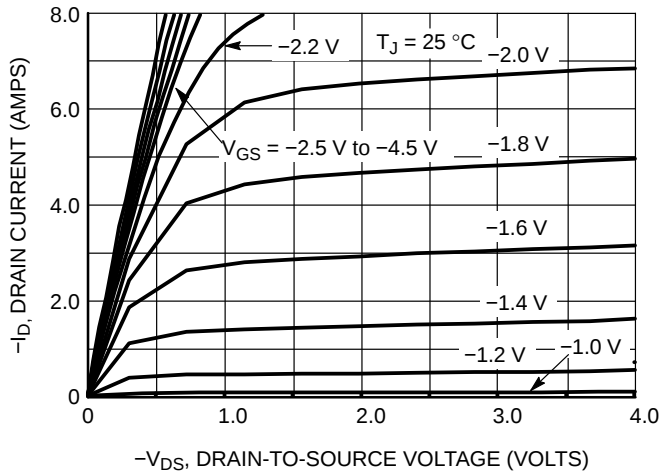


Figure 1. On-Region Characteristics

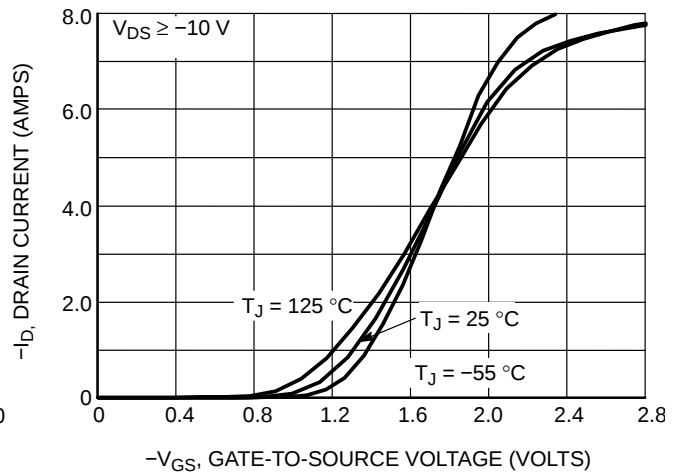


Figure 2. Transfer Characteristics

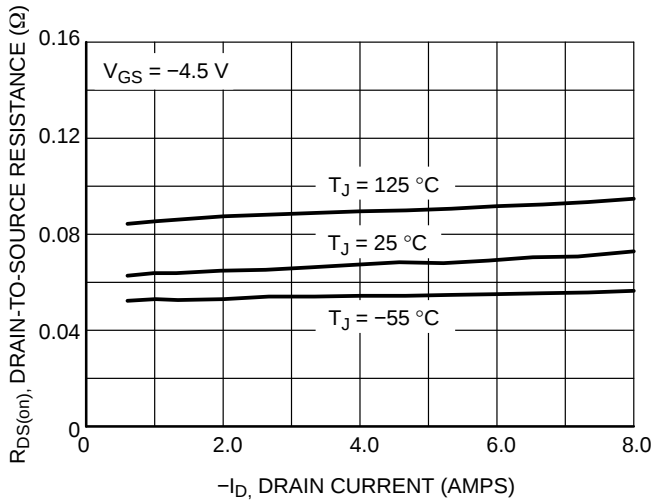


Figure 3. On-Resistance vs. Drain Current and Temperature

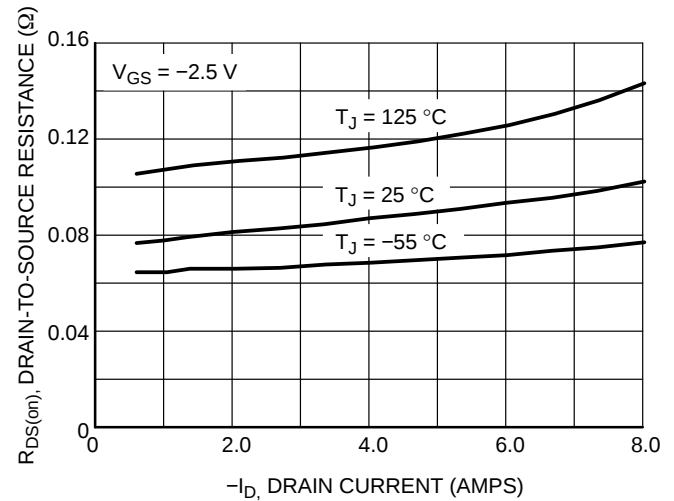


Figure 4. On-Resistance vs. Drain Current and Temperature

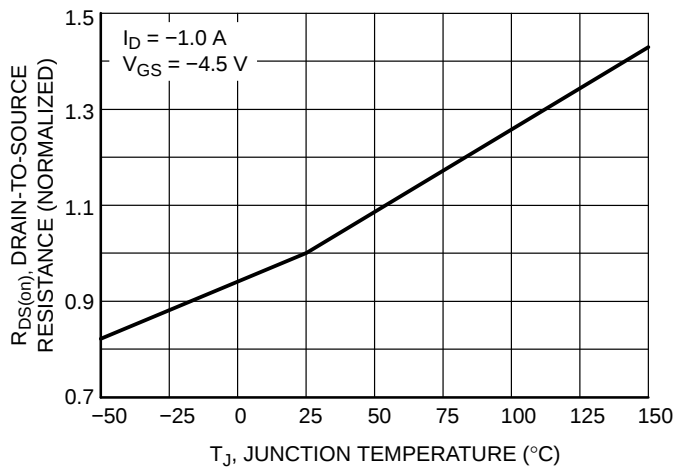


Figure 5. On-Resistance Variation with Temperature

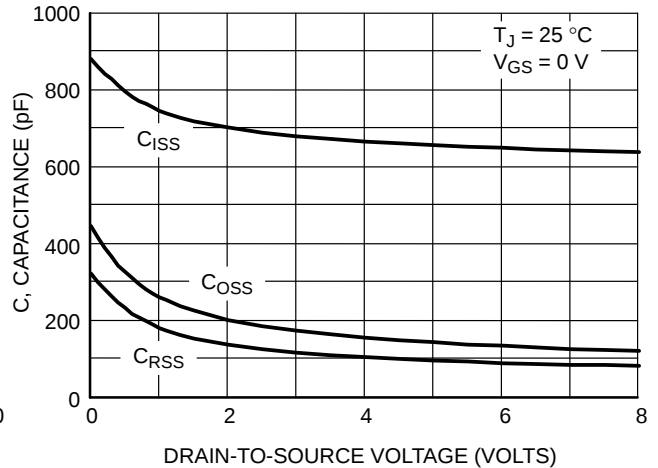


Figure 6. Capacitance Variation

TYPICAL ELECTRICAL CHARACTERISTICS

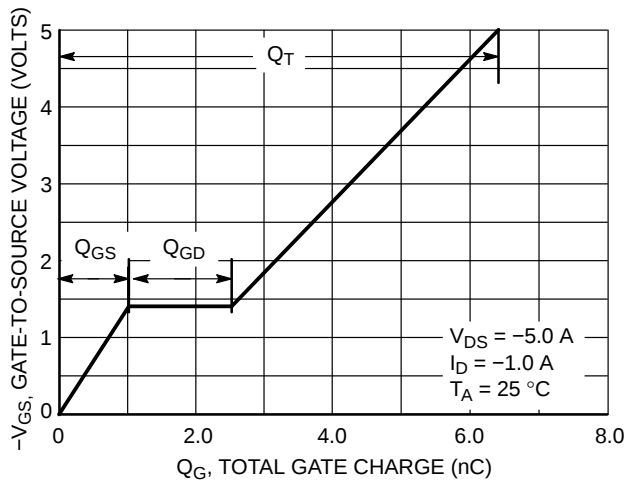


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Gate Charge

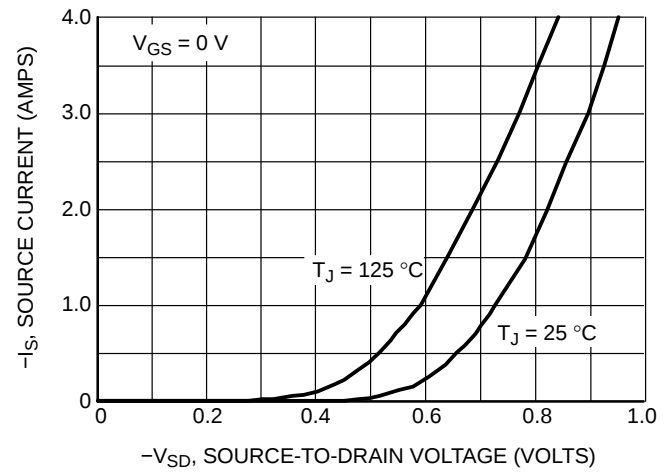


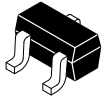
Figure 8. Diode Forward Voltage vs. Current

NTS2101P

REVISION HISTORY

Revision	Description of Changes	Date
3	Rebranded the document to onsemi format. NTS2101PT1 OPN marked as Discontinued.	2/4/2026

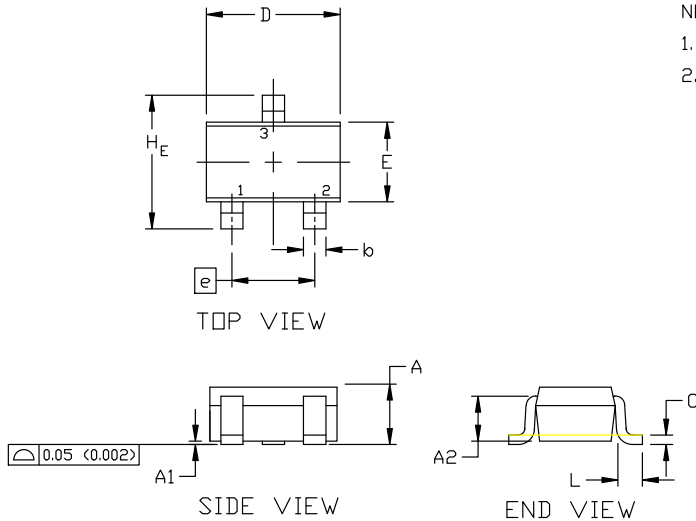
This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

DATE 11 OCT 2022

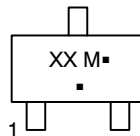


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

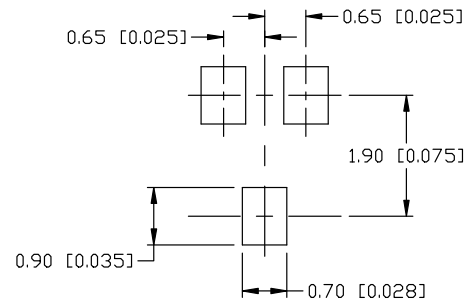
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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